AMENDMENTS TO THE CLAIMS

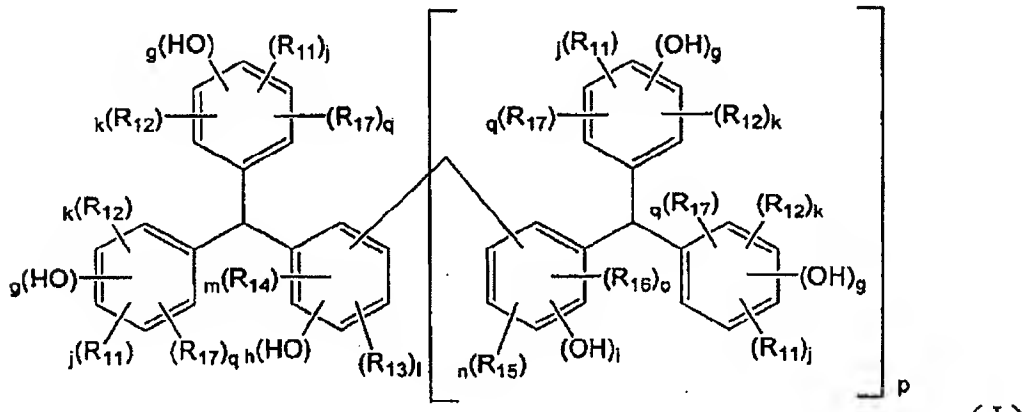
1. (**Previously presented**) A base material for a pattern-forming material, comprising a low molecular weight compound (X1), which is formed from a polyhydric phenol compound (x) that comprises two or more phenolic hydroxyl groups and satisfies conditions (1), (2), and (3) described below, wherein either a portion of, or all of, said phenolic hydroxyl groups are protected with acid dissociable, dissolution inhibiting groups, wherein

the proportion within said base material of said low molecular weight compound (X1), in which either a portion of, or all of, said polyhydric phenol compound (x) are protected with acid dissociable, dissolution inhibiting groups, is greater than 80% by weight:

(1) a molecular weight within a range from 450 to 1,500, (2) a molecular weight dispersity of no more than 1.5, and (3) an ability to form an amorphous film using a spin coating method.

2. (**Original**) A base material for a pattern-forming material according to claim 1, wherein said polyhydric phenol compound (x) is one or more compounds selected from the group consisting of polyhydric phenol compounds represented by general formulas (I), (II), and (III) shown below:

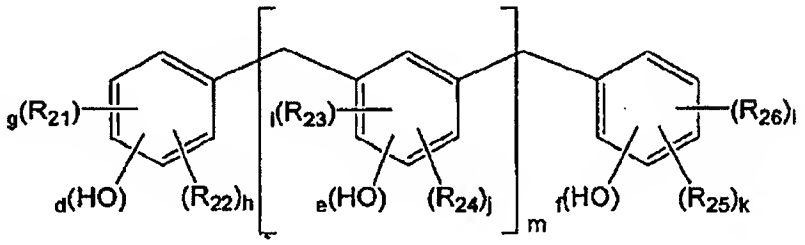
[Formula 1]



[wherein, R_{11} through R_{17} each represent, independently, an alkyl group or aromatic hydrocarbon group of 1 to 10 carbon atoms, and these structures may also include a hetero atom; g and j each represent, independently, an integer of 1 or greater, k and q each represent either 0 or an integer of 1 or greater, and g+j+k+q is no greater than 5; h is an integer of 1 or greater, l and m each

represent, independently, either 0 or an integer of 1 or greater, and h+l+m is no greater than 4; i is an integer of 1 or greater, n and o each represent, independently, either 0 or an integer of 1 or greater, and i+n+o is no greater than 4; and p is either 0 or 1],

[Formula 2]



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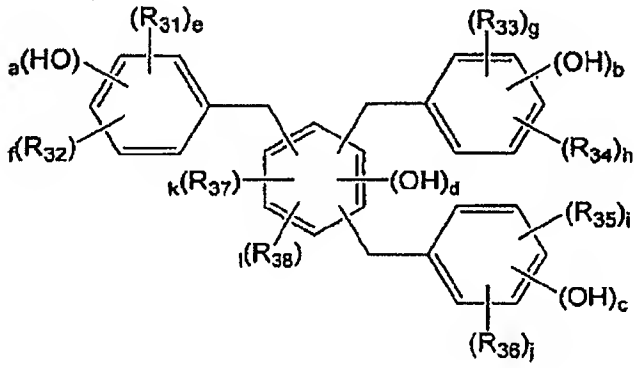
[wherein, R_{21} through R_{26} each represent, independently, an alkyl group or aromatic hydrocarbon group of 1 to 10 carbon atoms, and these structures may also include a hetero atom; d and g each represent, independently, an integer of 1 or greater, h represents either 0 or an integer of 1 or greater, and d+g+h is no greater than 5; e represents an integer of 1 or greater, i and j each represent, independently, either 0 or an integer of 1 or greater, and e+i+j is no greater than 4; f and k each represent, independently, an integer of 1 or greater, l represents either 0 or an integer of 1 or greater, and f+k+l is no greater than 5; and m is an integer from 1 to 20],

[Formula 3]



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[wherein, R_{31} through R_{38} each represent, independently, an alkyl group or aromatic hydrocarbon group of 1 to 10 carbon atoms, and these structures may also include a hetero atom; a and e each represent, independently, an integer of 1 or greater, f represents either 0 or an integer of 1 or greater, and a+e+f is no greater than 5; b and h each represent, independently, an integer of 1 or greater, g represents either 0 or an integer of 1 or greater, and b+h+g is no greater than 5; c and i

each represent, independently, an integer of 1 or greater, j represents either 0 or an integer of 1 or greater, and c+i+j is no greater than 5; d represents an integer of 1 or greater, k and l each represent, independently, either 0 or an integer of 1 or greater, and d+k+l is no greater than 3].

3. (**Original**) A positive resist composition, comprising a base material component (A), which contains acid dissociable, dissolution inhibiting groups and displays increased alkali solubility under action of acid, and (B) an acid generator that generates acid on exposure, wherein

said base material component (A) is a base material for a pattern-forming material according to claim 1.

4. (**Original**) A positive resist composition, comprising a base material component (A), which contains acid dissociable, dissolution inhibiting groups and displays increased alkali solubility under action of acid, and (B) an acid generator that generates acid on exposure, wherein

said base material component (A) is a base material for a pattern-forming material according to claim 2.

5. (**Original**) A positive resist composition according to claim 3, further comprising a nitrogen-containing organic compound (D).

6. (**Original**) A method of forming a resist pattern comprising the steps of applying a positive resist composition according to claim 3 to a substrate, conducting a prebake, performing selective exposure, conducting PEB (post exposure baking), and performing alkali developing to form a resist pattern.

7. (**Original**) A method of forming a resist pattern comprising the steps of applying a positive resist composition according to claim 4 to a substrate, conducting a prebake, performing selective exposure, conducting PEB (post exposure baking), and performing alkali developing to form a resist pattern.

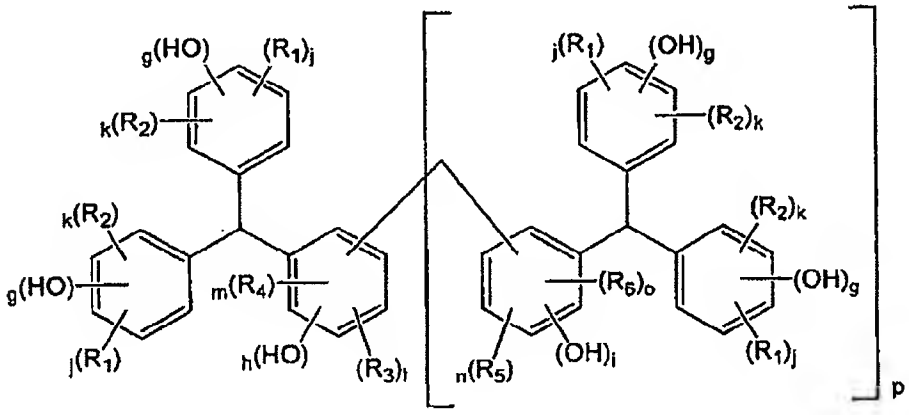
8. (**Previously presented**) A base material for a pattern-forming material, comprising a protected material (Y1), which is formed from a polyhydric phenol compound (y) that comprises two or more phenolic hydroxyl groups and has a molecular weight within a range from 450 to 1,500, in which either a portion of, or all of, said phenolic hydroxyl groups are protected with acid dissociable, dissolution inhibiting groups, and wherein

the proportion within said base material of said protected material (Y1) is greater than 80% by weight, wherein the proportion within said base material of an unprotected material (Y2), in which said phenolic hydroxyl groups of said polyhydric phenol compound (y) are not protected with acid dissociable, dissolution inhibiting groups, is no more than 20% by weight.

9. (**Original**) A base material for a pattern-forming material according to claim 8, wherein a molecular weight dispersity (Mw/Mn) of said polyhydric phenol compound (y) is no more than 1.5.

10. (**Original**) A base material for a pattern-forming material according to claim 8, wherein said polyhydric phenol compound (y) is a compound represented by a general formula (I) shown below:

[Formula 4]



[wherein, R_1 through R_6 each represent, independently, an alkyl group or aromatic hydrocarbon group of 1 to 10 carbon atoms, and these structures may also include a hetero atom; g and j each represent, independently, an integer of 1 or greater, k represents either 0 or an integer of 1 or greater, and g+j+k is no greater than 5; h is an integer of 1 or greater, l and m each represent, independently, either 0 or an integer of 1 or greater, and h+l+m is no greater than 4; i is an

integer of 1 or greater, n and o each represent, independently, either 0 or an integer of 1 or greater, and i+n+o is no greater than 4; and p is either 0 or 1].

11. (**Original**) A positive resist composition, comprising a base material component (A), which contains acid dissociable, dissolution inhibiting groups and displays increased alkali solubility under action of acid, and (B) an acid generator that generates acid on exposure, wherein

said base material component (A) is a base material for a pattern-forming material according to claim 8.

12. (**Original**) A positive resist composition, comprising a base material component (A), which contains acid dissociable, dissolution inhibiting groups and displays increased alkali solubility under action of acid, and (B) an acid generator that generates acid on exposure, wherein

said base material component (A) is a base material for a pattern-forming material according to claim 10.

13. (**Original**) A positive resist composition according to claim 11, further comprising a nitrogen-containing organic compound (D).

14. (**Original**) A method of forming a resist pattern comprising the steps of applying a positive resist composition according to claim 11 to a substrate, conducting a prebake, performing selective exposure, conducting PEB (post exposure baking), and performing alkali developing to form a resist pattern.

15. (**Original**) A method of forming a resist pattern comprising the steps of applying a positive resist composition according to claim 12 to a substrate, conducting a prebake, performing selective exposure, conducting PEB (post exposure baking), and performing alkali developing to form a resist pattern.

16. (**Previously presented**) A base material for a pattern-forming material according to claim 1, wherein the proportion within said base material of said low molecular weight compound (X1), which is formed from a polyhydric phenol compound (x), wherein either a portion of, or all of, said phenolic hydroxyl groups are protected with acid dissociable, dissolution inhibiting groups, is 100% by weight.

17. (**Previously presented**) A base material for a pattern-forming material according to claim 1, wherein the proportion of phenolic hydroxyl groups is within a range of from 5 to 50 mol%.

18. (**Previously presented**) A base material for a pattern-forming material according to claim 8, wherein a proportion within said base material of said protected material (Y1) is 100% by weight.

19. (**Previously presented**) A base material for a pattern-forming material according to claim 8, wherein the proportion of phenolic hydroxyl groups is within a range of from 5 to 50 mol%.

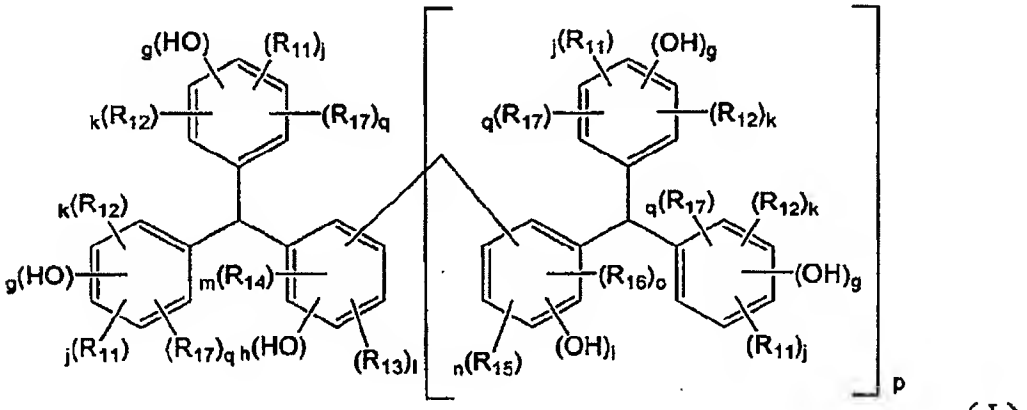
20. (**New**) A base material for a pattern-forming material according to claim 1, comprising a low molecular weight compound (X1), which is formed from a polyhydric phenol compound (x) that comprises two or more phenolic hydroxyl groups and satisfies conditions (1), (2), and (3) described below, wherein either a portion of, or all of, said phenolic hydroxyl groups are protected with acid dissociable, dissolution inhibiting groups, wherein

the proportion within said base material of said low molecular weight compound (X1), in which either a portion of, or all of, said polyhydric phenol compound (x) is protected with acid dissociable, dissolution inhibiting groups, is greater than 80% by weight:

(1) a molecular weight within a range from 450 to 1,500, (2) a molecular weight dispersity of no more than 1.5, and (3) an ability to form an amorphous film using a spin coating method,

wherein said polyhydric phenol compound (x) is one or more compounds selected from the group consisting of polyhydric phenol compounds represented by general formulas (I) shown below:

[Formula 1]



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[wherein, R_{11} through R_{17} each represent, independently, an alkyl group or aromatic hydrocarbon group of 1 to 10 carbon atoms, and these structures may also include a hetero atom; g and j each represent, independently, an integer of 1 or greater, k and q each represent either 0 or an integer of 1 or greater, and g+j+k+q is no greater than 5; h is an integer of 1 or greater, l and m each represent, independently, either 0 or an integer of 1 or greater, and h+l+m is no greater than 4; i is an integer of 1 or greater, n and o each represent, independently, either 0 or an integer of 1 or greater, and i+n+o is no greater than 4; and p is 1].